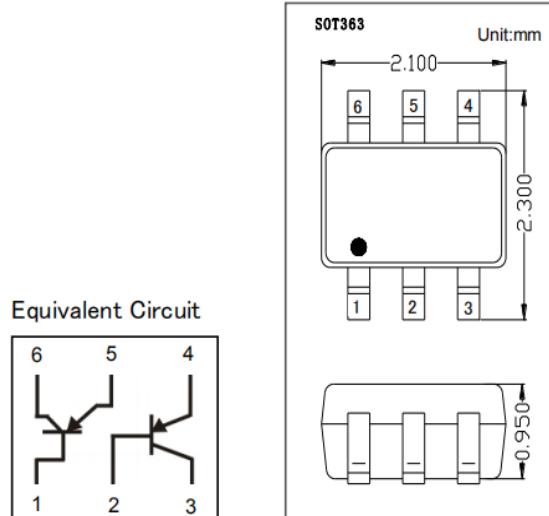


## Dual PNP Small Signal Transistors

### MMDT3906

- ◊ Epoxy meets UL 94 V-0 flammability rating
- ◊ Lead Free Finish/RoHS Compliant
- ◊ For Switching and AF Amplifier Applications
- ◊ Rugged and reliable



#### Maximum Ratings ( $T_a = 25^\circ\text{C}$ )

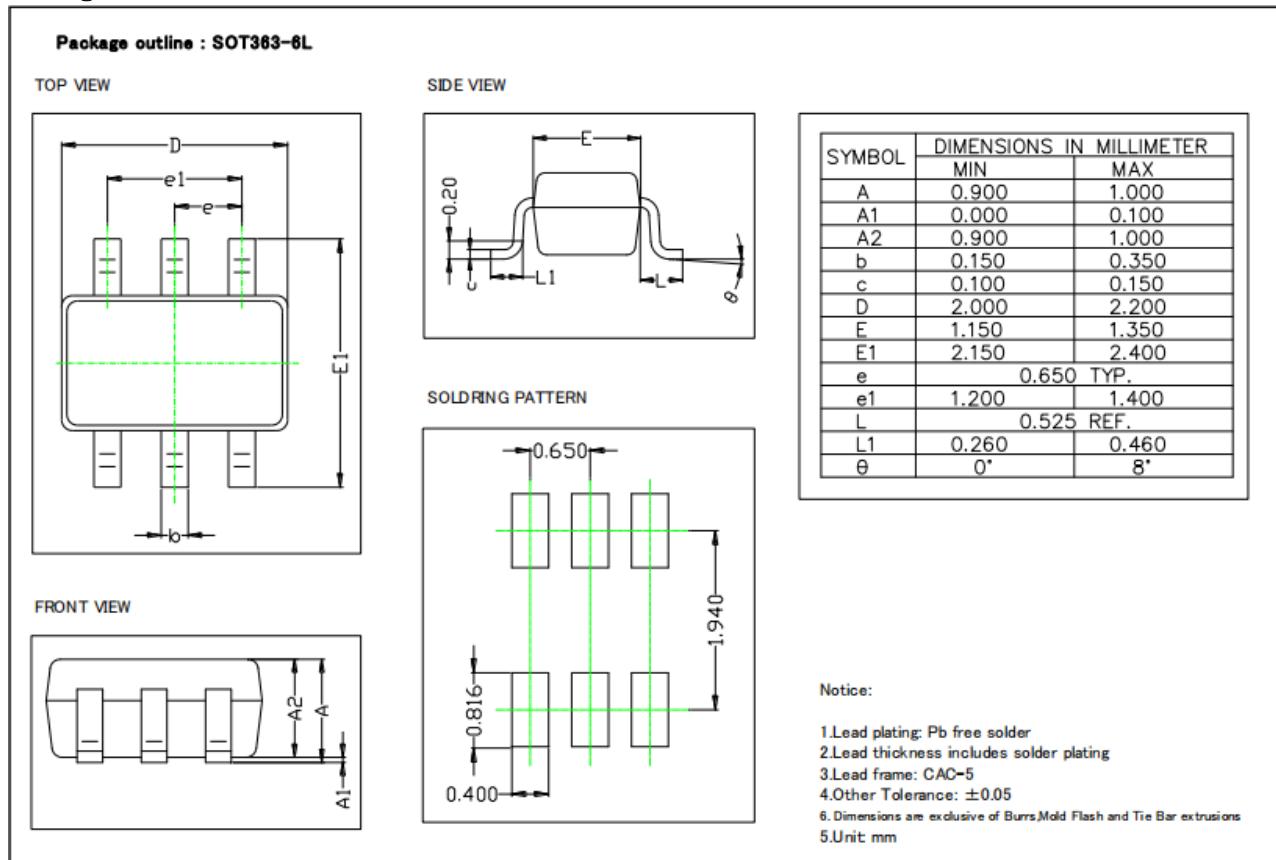
Symbol	Parameter	Value	Units
$V_{CBO}$	Collector–Base Voltage	-40	V
$V_{CEO}$	Collector–Emitter Voltage	-40	V
$V_{EBO}$	Emitter–Base Voltage	-5	V
$P_c$	Collector Power Dissipation	200	mW
$I_c$	Collector Current – Continuous	-200	mA
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{STG}$	Storage Temperature	-55 to 150	$^\circ\text{C}$
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	625	$^\circ\text{C}/\text{W}$

#### Electrical Characteristics ( $T_a = 25^\circ\text{C}$ )

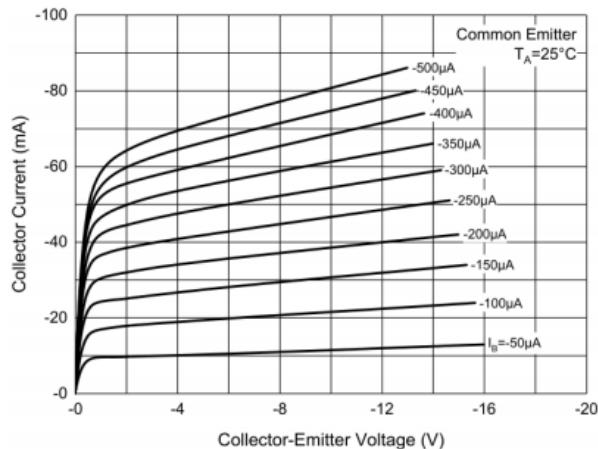
Symbol	Parameter	Test Conditions	Min	Max	Units
$V_{(BR)CBO}$	Collector–Base Breakdown Voltage	$I_C = -10 \mu\text{A}, I_E = 0$	-40		V
$V_{(BR)CEO}$	Collector–Emitter Breakdown Voltage	$I_C = -1\text{mA}, I_B = 0$	-40		V
$V_{(BR)EBO}$	Emitter–Base Breakdown Voltage	$I_E = -10 \mu\text{A}, I_C = 0$	-5		V
$I_{BL}$	Base Cutoff Current	$V_{CE} = -30\text{V}, V_{BE(OFF)} = -3\text{V}$		-50	nA
$I_{CEX}$	Collector Cutoff Current	$V_{CE} = -30\text{V}, V_{BE(OFF)} = -3\text{V}$		-50	nA
$V_{CE(sat)}$	Collector–Emitter Saturation Voltage	$I_C = -10\text{mA}, I_B = -1\text{mA}$		-0.25	V
		$I_C = -50\text{mA}, I_B = -5\text{mA}$		-0.4	
$V_{BE(sat)}$	Base–Emitter Saturation Voltage	$I_C = -10\text{mA}, I_B = -1\text{mA}$	-0.65	-0.85	V
		$I_C = -50\text{mA}, I_B = -5\text{mA}$		-0.95	

$h_{FE}$	DC Current Gain	$V_{CE} = -1V, I_C = -0.1mA$	60		
		$V_{CE} = -1V, I_C = -1mA$	80		
		$V_{CE} = -1V, I_C = -10mA$	100	300	
		$V_{CE} = -1V, I_C = -50mA$	60		
		$V_{CE} = -1V, I_C = -100mA$	30		
$f_T$	Transition Frequency	$V_{CE} = -20V, I_C = -10mA, f = 100MHz$	250		MHz
$C_{ob}$	Output Capacitance	$V_{CB} = -5V, I_E = 0, f = 1MHz$		4.5	pF
$t_d$	Delay Time	$V_{CC} = -3V, I_C = -10mA, V_{BE(OFF)} = -0.5V, I_{B1} = -1mA$		35	nS
$t_r$	Rise Time			35	nS
$t_s$	Storage Time	$V_{CC} = -3V, I_C = -10mA, I_{B1} = -I_{B2} = -1mA$		225	nS
$t_f$	Fall Time			75	nS

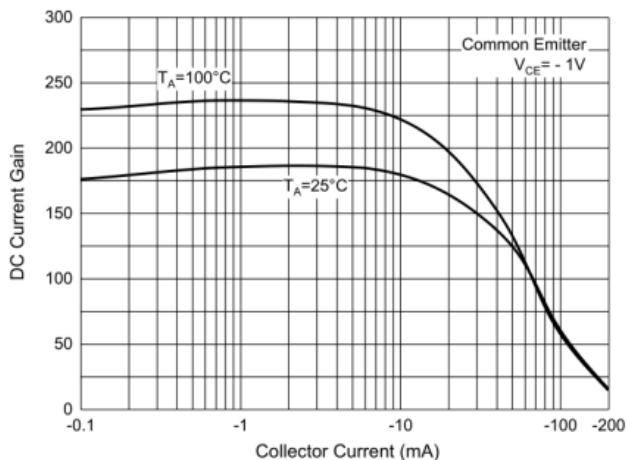
### Package Dimensions



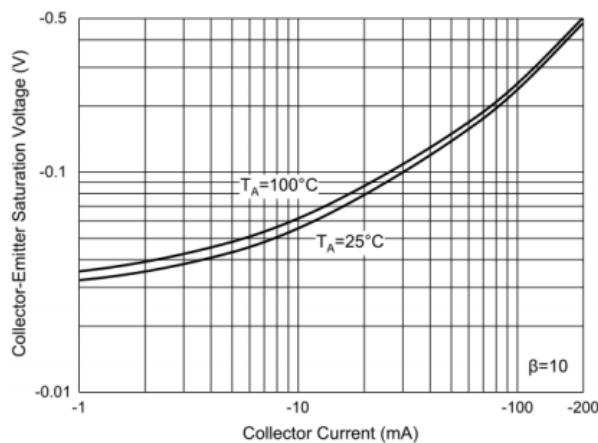
### Typical Characteristics



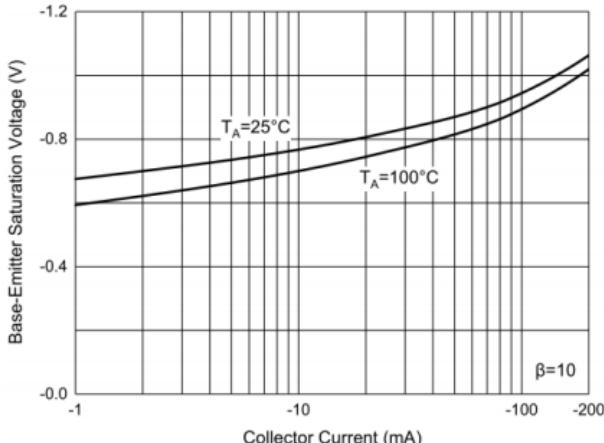
Static Characteristic



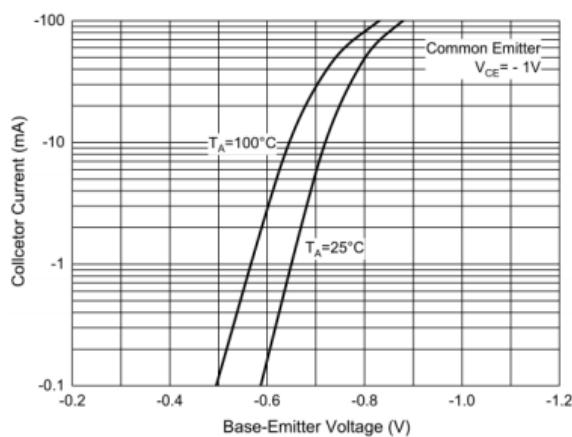
DC Current Gain Characteristics



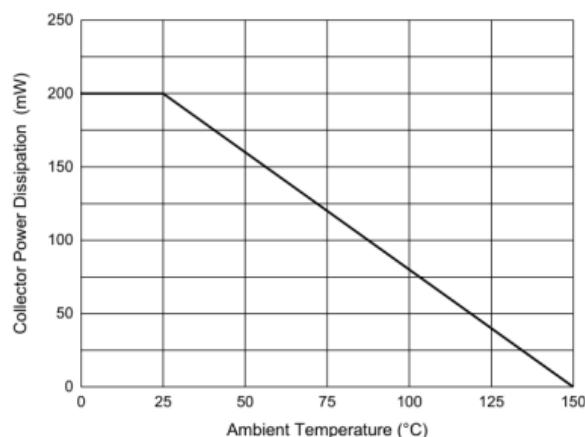
Collector-Emitter Saturation Voltage Characteristics



Base-Emitter Saturation Voltage Characteristics



Base-Emitter Voltage Characteristics



Collector Power Derating Curve